

# ZXTN2010G

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## 60V NPN MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

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### SUMMARY

$BV_{CEO} = 60V$  ;  $R_{SAT} = 35m\Omega$ ;  $I_C = 6A$

### DESCRIPTION

Packaged in the SOT223 outline this new low saturation 60V NPN transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.



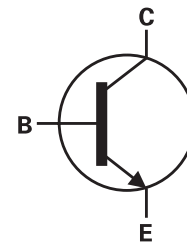
SOT223

### FEATURES

- Extremely low equivalent on-resistance;  $R_{SAT} = 35mV$  at 6A
- 6 amps continuous current
- Up to 20 amps peak current
- Very low saturation voltages
- Excellent  $h_{FE}$  characteristics up to 10 amps

### APPLICATIONS

- Emergency lighting circuits
- Motor driving (including DC fans)
- Solenoid, relay and actuator drivers
- DC Modules
- Backlight Inverters



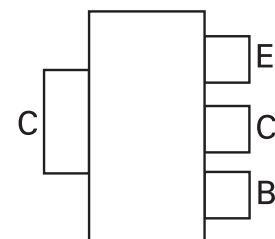
### ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXTN2010GTA	7"	12mm	1000 units
ZXTN2010GTC	13"	embossed	4000 units

### DEVICE MARKING

ZXTN  
2010

### PINOUT



TOP VIEW

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## ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Collector-base voltage	$BV_{CBO}$	150	V
Collector-emitter voltage	$BV_{CEO}$	60	V
Emitter-base voltage	$BV_{EBO}$	7	V
Continuous collector current <sup>(a)</sup>	$I_C$	6	A
Peak pulse current	$I_{CM}$	20	A
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(a)</sup>	$P_D$	3.0	W
Linear derating factor		24	mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(b)</sup>	$P_D$	1.6	W
Linear derating factor		12.8	mW/°C
Operating and storage temperature range	$T_j, T_{stg}$	-55 to +150	°C

## THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to ambient <sup>(a)</sup>	$R_{\theta JA}$	42	°C/W

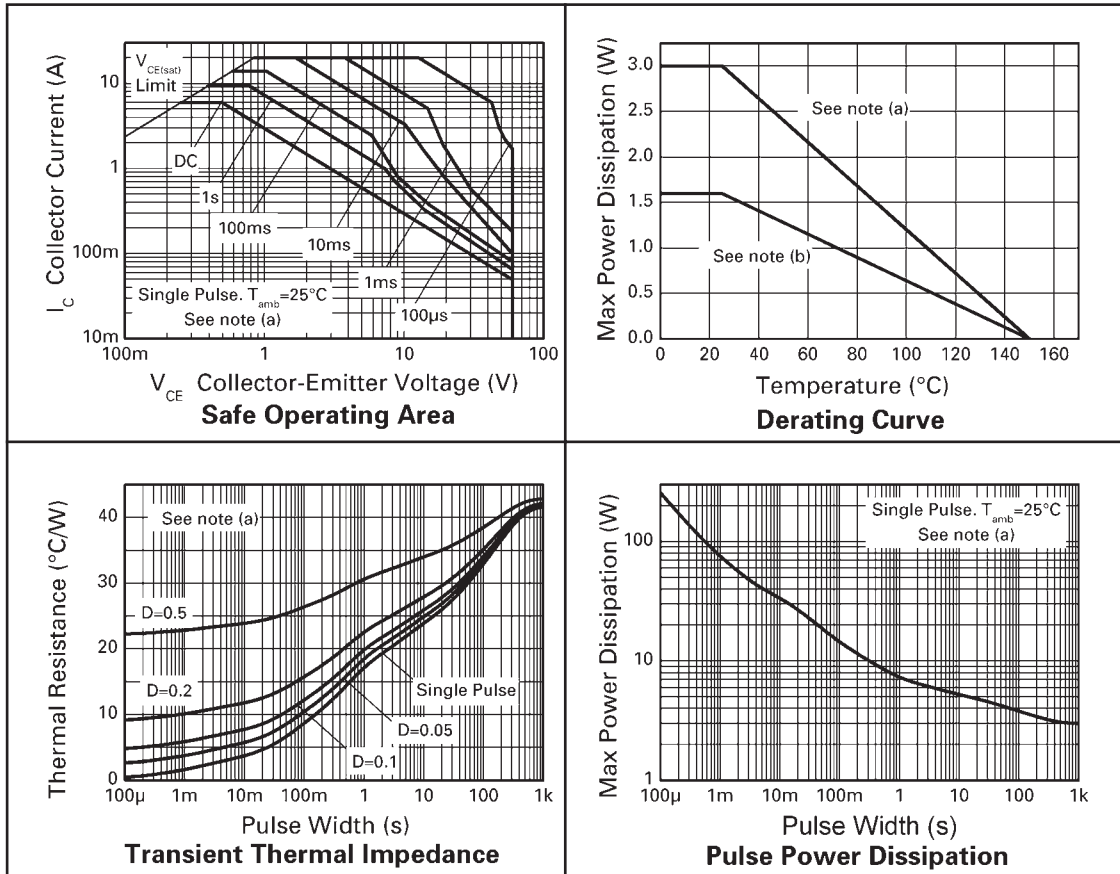
### NOTES

(a) For a device surface mounted on 52mm x 52mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

(b) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

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## CHARACTERISTICS



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## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

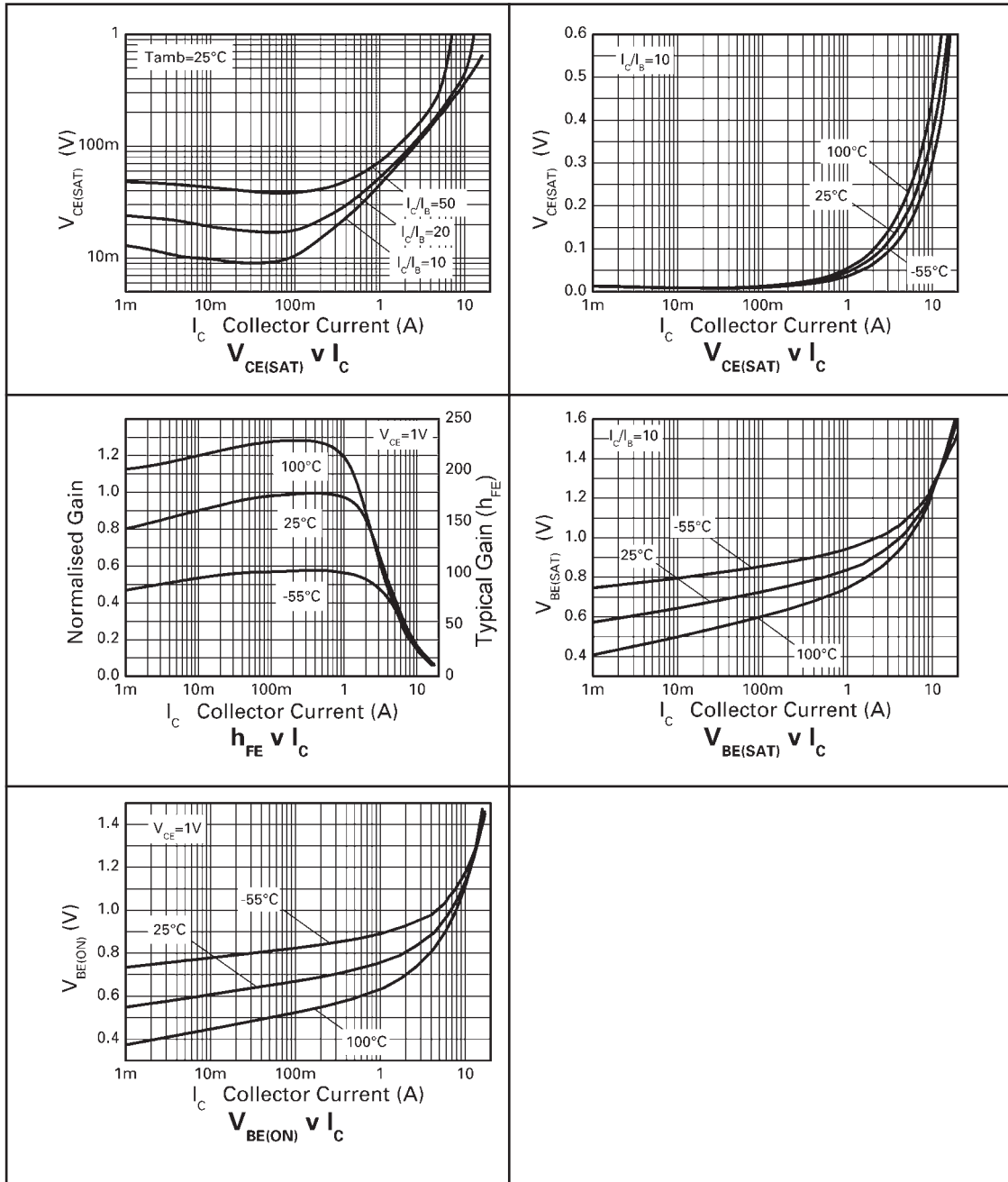
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Collector-base breakdown voltage	$BV_{CBO}$	150	190		V	$I_C=100\mu\text{A}$
Collector-emitter breakdown voltage	$BV_{CER}$	150	190		V	$I_C=1\mu\text{A}$ , $R_B\leq 1\text{k}\Omega$
Collector-emitter breakdown voltage	$BV_{CEO}$	60	80		V	$I_C=10\text{mA}^*$
Emitter-base breakdown voltage	$BV_{EBO}$	7	8.1		V	$I_E=100\mu\text{A}$
Collector cut-off current	$I_{CBO}$			50 0.5	nA $\mu\text{A}$	$V_{CB}=120\text{V}$ $V_{CB}=120\text{V}$ , $T_{amb}=100^{\circ}\text{C}$
Collector cut-off current	$I_{CER}$ $R\leq 1\text{k}\Omega$			100 0.5	nA $\mu\text{A}$	$V_{CB}=120\text{V}$ $V_{CB}=120\text{V}$ , $T_{amb}=100^{\circ}\text{C}$
Emitter cut-off current	$I_{EBO}$			10	nA	$V_{EB}=6\text{V}$
Collector-emitter saturation voltage	$V_{CE(SAT)}$		20 45 50 100 210	30 60 70 135 260	mV	$I_C=100\text{mA}$ , $I_B=5\text{mA}^*$ $I_C=1\text{A}$ , $I_B=100\text{mA}^*$ $I_C=1\text{A}$ , $I_B=50\text{mA}^*$ $I_C=2\text{A}$ , $I_B=50\text{mA}^*$ $I_C=6\text{A}$ , $I_B=300\text{mA}^*$
Base-emitter saturation voltage	$V_{BE(SAT)}$		1000	1100	mV	$I_C=6\text{A}$ , $I_B=300\text{mA}^*$
Base-emitter turn-on voltage	$V_{BE(ON)}$		940	1050	mV	$I_C=6\text{A}$ , $V_{CE}=1\text{V}^*$
Static forward current transfer ratio	$H_{FE}$	100 100 55 20	200 200 105 40	300		$I_C=10\text{mA}$ , $V_{CE}=1\text{V}^*$ $I_C=2\text{A}$ , $V_{CE}=1\text{V}^*$ $I_C=5\text{A}$ , $V_{CE}=1\text{V}^*$ $I_C=10\text{A}$ , $V_{CE}=1\text{V}^*$
Transition frequency	$f_T$		130		MHz	$I_C=100\text{mA}$ , $V_{CE}=10\text{V}$ $f=50\text{MHz}$
Output capacitance	$C_{OBO}$		31		pF	$V_{CB}=10\text{A}$ , $f=1\text{MHz}^*$
Switching times	$t_{ON}$ $t_{OFF}$		42 760		ns	$I_C=1\text{A}$ , $V_{CC}=10\text{V}$ , $I_{B1}=I_{B2}=100\text{mA}$

### NOTES

(1) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

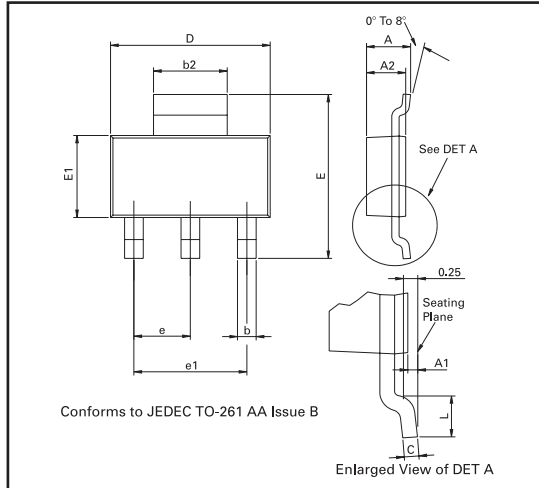
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## TYPICAL CHARACTERISTICS

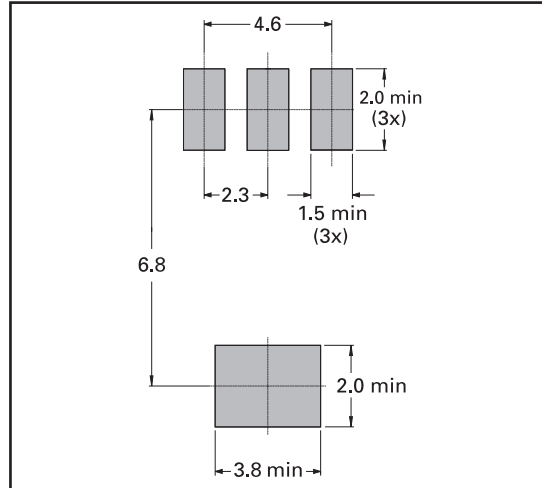


# ZXTN2010G

## PACKAGE OUTLINE



## PAD LAYOUT DETAILS



Controlling dimensions are in millimeters. Approximate conversions are given in inches

## PACKAGE DIMENSIONS

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	e	2.30 BSC		0.0905 BSC	
A1	0.02	0.10	0.0008	0.004	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

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Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Streitfeldstraße 19 D-81673 München Germany	Zetex Inc 700 Veterans Memorial Hwy Hauppauge, NY 11788 USA	Zetex (Asia) Ltd 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park Chadderton, Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 <a href="mailto:europe.sales@zetex.com">europe.sales@zetex.com</a>	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 <a href="mailto:usa.sales@zetex.com">usa.sales@zetex.com</a>	Telephone: (852) 26100 611 Fax: (852) 24250 494 <a href="mailto:asia.sales@zetex.com">asia.sales@zetex.com</a>	Telephone (44) 161 622 4444 Fax: (44) 161 622 4446 <a href="mailto:hq@zetex.com">hq@zetex.com</a>

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